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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
09/696,826	10/25/2000	William M. Clark, Jr.	B-3650 617089-5	4721	
7.	590 03/27/2003				
Richard P Berg Esq			EXAMINER		
LADAS & PAI 5670 Wilshire I			TRAN, T	TRAN, THIEN F	
Suite 2100 Los Angeles, CA 90036-5679			ART UNIT	PAPER NUMBER	
<i>5</i> ,			2811	2811	
			DATE MAILED: 03/27/2003		

Please find below and/or attached an Office communication concerning this application or proceeding.

PTO-90C (Rev. 07-01)

	Application No.	Applicant(s)	- 44
	09/696,826	CLARK, JR. ET AL.	
Office Action Summary	Examin r	Art Unit	
	Thien Tran	2811	
The MAILING DATE of this communication app Period for Reply	ears on the cover sh t with th	correspond nc addres	s
A SHORTENED STATUTORY PERIOD FOR REPLY THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a reply If NO period for reply is specified above, the maximum statutory period w Failure to reply within the set or extended period for reply will, by statute, - Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	36(a). In no event, however, may a reply be within the statutory minimum of thirty (30) illiapply and will expire SIX (6) MONTHS ficuse the application to become ABANDC	e timety filed days will be considered timely. om the mailing date of this commu	nication.
Status			
1) Responsive to communication(s) filed on			
<i>,</i>	is action is non-final.		
3) Since this application is in condition for allowated closed in accordance with the practice under a Disposition of Claims	ince except for formal matters, Ex parte Quayle, 1935 C.D. 11	, 453 O.G. 213.	ents is
4)⊠ Claim(s) <u>1-8 and 15-26</u> is/are pending in the a	polication		
4a) Of the above claim(s) is/are withdraw			
5) Claim(s) is/are allowed.			
6)⊠ Claim(s) <u>1-8 and 15-26</u> is/are rejected.			
7) Claim(s) is/are objected to.			
8) Claim(s) are subject to restriction and/or	r election requirement.		
Application Papers	•		
9) The specification is objected to by the Examine	г.		
10)☐ The drawing(s) filed on is/are: a)☐ accep	ted or b)□ objected to by the E	xaminer.	
Applicant may not request that any objection to the	e drawing(s) be held in abeyance.	See 37 CFR 1.85(a).	
11)☐ The proposed drawing correction filed on	is: a)□ approved b)□ disap	proved by the Examiner.	
If approved, corrected drawings are required in rep			
12) ☐ The oath or declaration is objected to by the Ex-	aminer.		
Priority under 35 U.S.C. §§ 119 and 120			
13) Acknowledgment is made of a claim for foreign	priority under 35 U.S.C. § 11	9(a)-(d) or (f).	
a) ☐ All b) ☐ Some * c) ☐ None of:			
 Certified copies of the priority documents 			
2. Certified copies of the priority documents			
 3. Copies of the certified copies of the prior application from the International But * See the attached detailed Office action for a list 	reau (PCT Rule 17.2(a)).		је
14) Acknowledgment is made of a claim for domesti			olication).
a) The translation of the foreign language pro			,
15) Acknowledgment is made of a claim for domesti			
Attachment(s)	4) Interview Sumn	nary (PTO-413) Paper No(s)	
 Notice of References Cited (PTO-892) Notice of Draftsperson's Patent Drawing Review (PTO-948) Information Disclosure Statement(s) (PTO-1449) Paper No(s) 	5) Notice of Inform	nal Patent Application (PTO-15)	

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DETAILED ACTION

Claim Objections

Claim 1 is objected to because of the following informalities: lines 7-8; "two spaced-apart regions" should be --two spaced-apart implanted regions--. Appropriate correction is required.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 1-8 and 15-26 are rejected under 35 U.S.C. 102(b) as being anticipated by Yahata (USPN 5,384,475).

Yahata discloses an interconnection structure (Figs. 3 and 4A-4C) for interconnecting two spaced-apart doped regions (8, 10a) of a common conductivity type (n-type) in a device comprising a first doped region 12 in the device forming a conducting channel between the two spaced-apart doped regions, the conducting channel being of the common conductivity type (n-type) and bridging a region between the two spaced-apart doped regions 8; and a second doped region 14 of opposite conductivity type (p-type) in the device, the second doped region being disposed between the two spaced-apart doped regions 8 of common conductivity type and overlying the conducting channel.

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The recitations "a camouflaged interconnection" and "in a manner which inhibits reverse engineering thereof" in the claim preamble specify an intended use or field of use. It has been held that in device claims, intended use must result in a structural difference between the claim invention and the prior art in order to patentably distinguish the claim invention from the prior art. If the prior art structure is capable of performing the intended use, then it meets the claim. In re Casey, 152 USPQ 235 (CCPA 1967); In re Otto, 136 USPQ 458, 459 (CCPA 1963). A claim containing a "recitation with respect to the manner in which a claimed apparatus is intended to be employed does not differentiate the claimed apparatus from a prior art apparatus" if the prior art apparatus teaches all the structural limitations of the claim. Ex parte Masham, 2 USPQ2d 1647 (Bd. Pat. App. & Inter. 1987). It is clear that Yahata discloses the same interconnection structure as claimed wherein a second doped region 14 of p-type is formed above the first doped region 12 of n-type. The second dope region 14 of Yahata hides and conceals the conducting channel 12; therefore, Yahata structure inherently discloses a camouflaged buried interconnect 12 which helps inhibit reverse engineering.

Regarding claims 2, 6, 16 and 20, the second doped region 14 overlying the conducting channel 12 has a larger area, when view in a direction normal to a major surface of the device, than has the conducting channel 12.

Regarding claims 3, 7, 17 and 21, the two spaced-apart doped regions form drain contacts, respectively of adjacent field effect transistors.

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Regarding claims 4 and 8, the second doped region 4 is provided in the device over regions having no conducting channels formed therein (see Fig. 4C).

Regarding claims 5 and 19, Yahata discloses a plurality of interconnects 12 each interconnecting selected doped regions of the plurality of spaced-apart doped regions, each interconnect comprising a buried conducting channel bridging a region between the selected doped regions. The doped region 14 of p-type is disposed over the plurality of interconnects which inherently camouflages the majority of the plurality of interconnects.

Regarding claim 15, Yahata discloses an interconnection structure for interconnecting two spaced-apart regions (8, 10a) of a common conductivity type (n-type) in a device comprising a first region 12 in the device disposed laterally of and in direct contact with the two spaced-apart regions, the first region being of the common conductivity type (n-type), the first region providing a buried conducting channel for the two spaced-apart regions; and a second region 14 of opposite conductivity type (p-type) in the device, the second region being disposed between the two spaced-apart regions of common conductivity type and overlying the first region to conceal the conducting channel.

Regarding claims 18 and 22, Yahata further discloses one additional spaced-apart region (9, 10b) of the common conductivity type (n-type), the additional space-apart region being spaced apart from the two spaced-apart regions (8, 10a); and one additional region 14 of the opposite conductivity type (p-type) in the device, the one additional region 14 being disposed laterally of and in contact with one of the two

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spaced-apart regions (8, 10a) and the additional spaced-apart region (9, 10b), wherein the one of the two spaced-apart regions (8, 10a) and the additional spaced-apart region (9, 10b) do not have the buried conducting channel formed therebetween.

Regarding claims 23-26, the second doped region 14 of p-type has a depth less than a depth of the first doped region 12.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Thien Tran whose telephone number is (703) 308-4108. The examiner can normally be reached on 8:30AM - 5:00PM Monday through Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Tom Thomas can be reached on (703) 308-2772. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 872-9318 for regular communications and (703) 872-9319 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

March 20, 2003

Thien Tran Patent Examiner

Technology Center 2800